



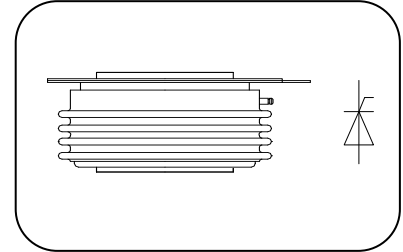
**Features**

- Interdigitated amplifying gates
- Fast turn-on and high di/dt
- Low switching losses

**Typical Applications**

- Inductive heating
- Electronic welders
- Self-commutated inverters

$I_{T(AV)}$       **1200A**  
 $V_{DRM}/V_{RRM}$     **2400~3000V**  
 $t_q$                 **30~60μs**  
 $I_{TSM}$              **16kA**  
 $I^2t$                 **1280 10<sup>3</sup>A<sup>2</sup>S**



SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T <sub>J</sub> (°C)	VALUE			UNIT
				Min	Type	Max	
I <sub>T(AV)</sub>	Mean on-state current	180° half sine wave 50Hz Double side cooled, T <sub>C</sub> =55°C	125		1200	1320	A
V <sub>DRM</sub> V <sub>RRM</sub>	Repetitive peak off-state voltage Repetitive peak reverse voltage	V <sub>DRM</sub> &V <sub>RRM</sub> , tp=10ms V <sub>DSM</sub> &V <sub>RSM</sub> = V <sub>DRM</sub> &V <sub>RRM</sub> +100V	125	2400		3000	V
I <sub>DRM</sub> I <sub>RRM</sub>	Repetitive peak current	V <sub>D</sub> = V <sub>DRM</sub> V <sub>R</sub> = V <sub>RRM</sub>	125			100	mA
I <sub>TSM</sub>	Surge on-state current	10ms half sine wave	125			16	kA
I <sup>2</sup> t	I <sup>2</sup> T for fusing coordination	V <sub>R</sub> =0.6V <sub>RRM</sub>					1280
V <sub>TO</sub>	Threshold voltage		125			1.67	V
r <sub>T</sub>	On-state slop resistance						0.32
V <sub>TM</sub>	Peak on-state voltage	I <sub>TM</sub> =3000A, F=26kN	25			3.2	V
dv/dt	Critical rate of rise of off-state voltage	V <sub>DM</sub> =0.67V <sub>DRM</sub>	125			1000	V/μs
di/dt	Critical rate of rise of on-state current	V <sub>DM</sub> = 67%V <sub>DRM</sub> , I <sub>TM</sub> =(2-3)I <sub>T(AV)</sub> , t=5s , Gate pulse t <sub>r</sub> ≤0.5μs I <sub>GM</sub> =1.5A f=50Hz	125			600	A/μs
Q <sub>rr</sub>	Recovery charge	I <sub>TM</sub> =1200A, tp=1000μs, di/dt=-20A/μs, V <sub>R</sub> =100V	125		750		μC
t <sub>q</sub>	Circuit commutated turn-off time	I <sub>TM</sub> =1200A, tp=1000μs, V <sub>R</sub> =100V dv/dt=30V/μs , di/dt=-20A/μs	125	30		60	μs
I <sub>GT</sub>	Gate trigger current	V <sub>A</sub> =12V, I <sub>A</sub> =1A	25	40		200	mA
V <sub>GT</sub>	Gate trigger voltage			0.9		2.5	V
I <sub>H</sub>	Holding current			20		300	mA
V <sub>GD</sub>	Non-trigger gate voltage	V <sub>DM</sub> =67%V <sub>DRM</sub>	125			0.3	V
R <sub>th(j-c)</sub>	Thermal resistance Junction to case	At 180° sine double side cooled Clamping force 26kN				0.018	°C /W
R <sub>th(c-h)</sub>	Thermal resistance case to heat sink					0.004	
F <sub>m</sub>	Mounting force			21		30	kN
T <sub>stg</sub>	Stored temperature			-40		140	°C
W <sub>t</sub>	Weight				600		g
Outline	KT60cT						

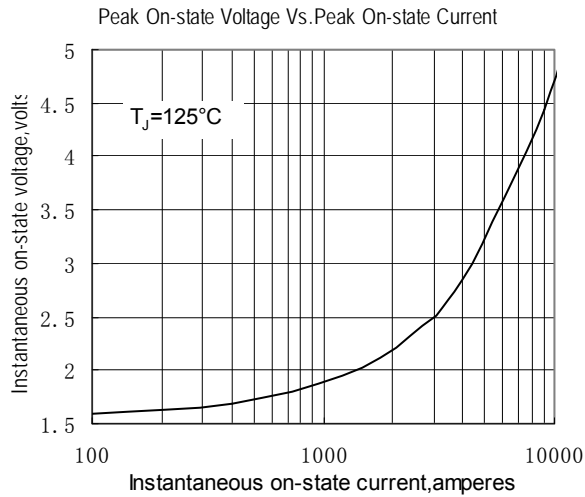


Fig.1

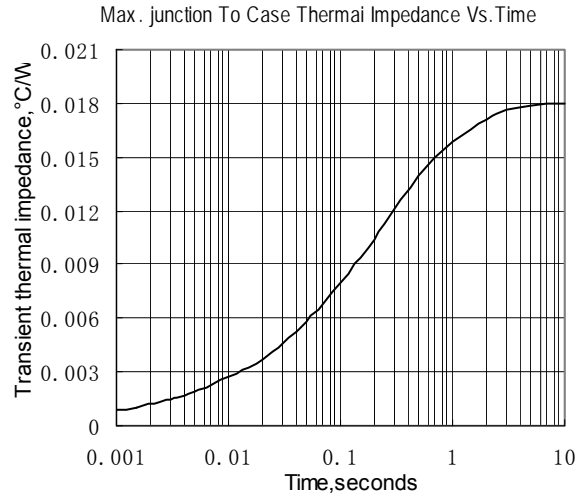


Fig.2

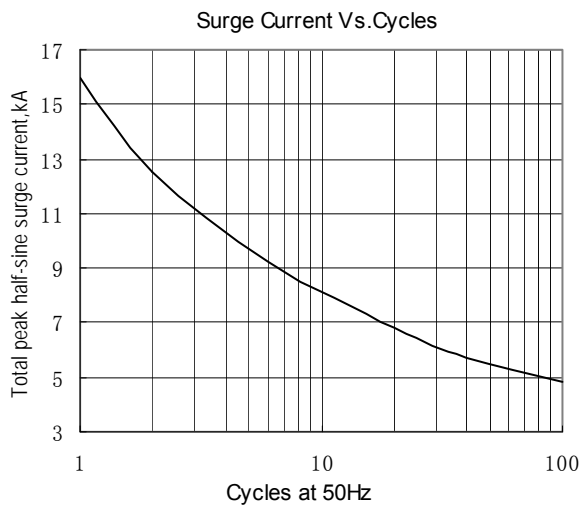


Fig.3

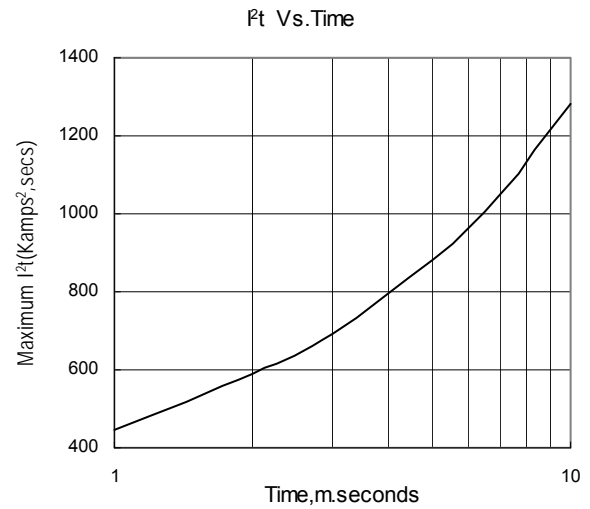
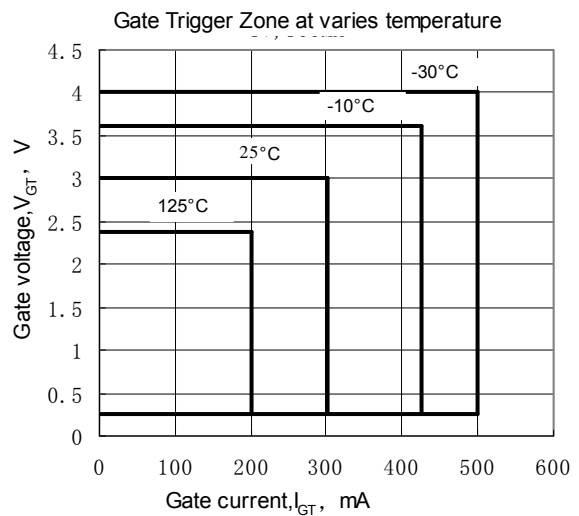
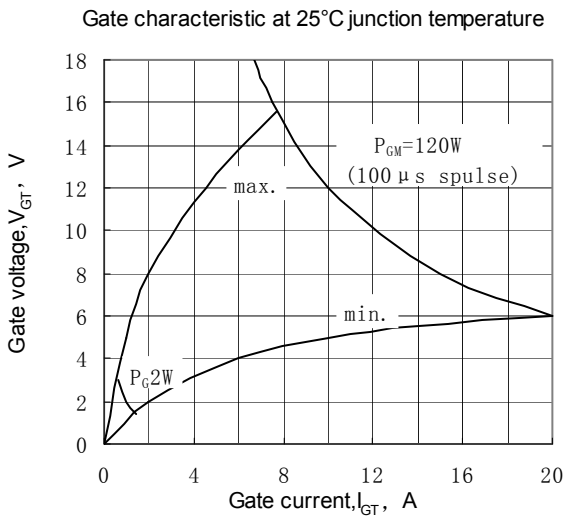
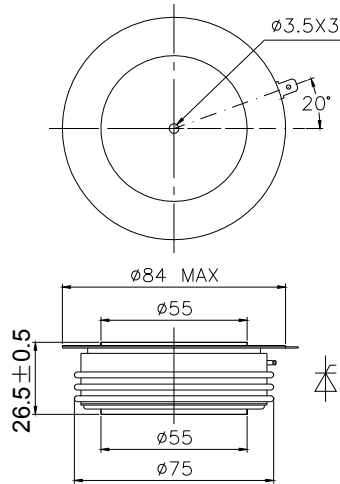


Fig.4





Outline: 图10-KT60cT



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